

Transistors

# 2.5V Drive Nch+Nch MOS FET

## QS6K1

●Structure

Silicon N-channel  
MOS FET

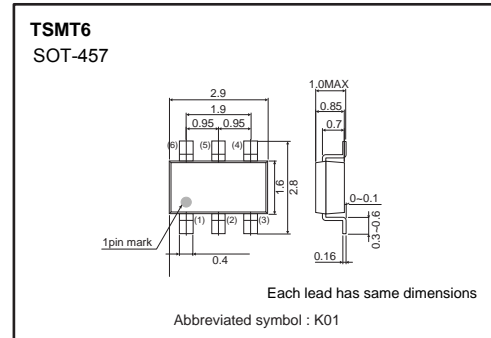
●Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (TSMT6).

●Application

Power switching, DC / DC converter.

●External dimensions (Unit : mm)



●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QS6K1		○

●Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2>

Parameter	Symbol	Limits	Unit
Drain-source voltage	$V_{DSS}$	30	V
Gate-source voltage	$V_{GSS}$	12	V
Drain current	Continuous	$I_D$	$\pm 1.0$ A
	Pulsed	$I_{DP}$ *1	$\pm 4.0$ A
Source current (Body diode)	Continuous	$I_S$	0.8 A
	Pulsed	$I_{SP}$ *1	4.0 A
Total power dissipation (Tc=25°C)	$P_D$ *2	1.25	W / TOTAL
		0.9	W / ELEMENT
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

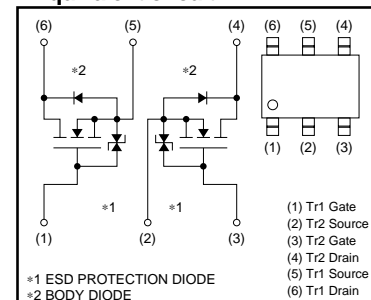
\*1  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$   
\*2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th}(ch-a)$ *	100	°C / W / TOTAL
		139	°C / W / ELEMENT

\* Mounted on a ceramic board

●Equivalent circuit



\*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

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### ●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	10	$\mu A$	$V_{GS}=12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	1	$\mu A$	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.5	–	1.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	170	238	m $\Omega$	$I_D=1.0A, V_{GS}=4.5V$
		–	180	252		$I_D=1.0A, V_{GS}=4.0V$
		–	260	364		$I_D=1.0A, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	1.0	–	–	S	$I_D=1.0A, V_{DS}=10V$
Input capacitance	$C_{iss}$	–	77	–	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	–	25	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	–	15	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	7	–	ns	$I_D=500mA, V_{DD} \approx 15V$
Rise time	$t_r$ *	–	7	–	ns	$V_{GS}=4.5V$
Turn-off delay time	$t_{d(off)}$ *	–	15	–	ns	$R_L=30.0\Omega$
Fall time	$t_f$ *	–	6	–	ns	$R_G=10\Omega$
Total gate charge	$Q_g$ *	–	1.7	2.4	nC	$V_{DD} \approx 15V$
Gate-source charge	$Q_{gs}$ *	–	0.4	–	nC	$V_{GS}=4.5V$
Gate-drain charge	$Q_{gd}$ *	–	0.4	–	nC	$I_D=1.0A$

\*Pulsed

### ●Body diode characteristics (Source-Drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}$ *	–	–	1.2	V	$I_S=3.2A, V_{GS}=0V$

\*Pulsed

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●Electrical characteristic curves

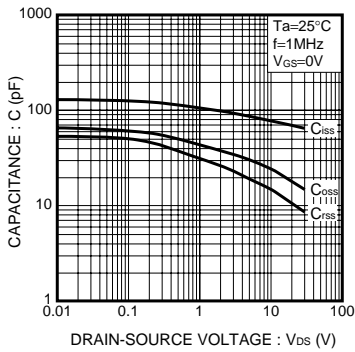


Fig.1 Typical Capacitance vs. Drain-Source Voltage

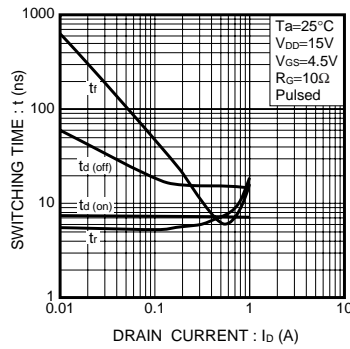


Fig.2 Switching Characteristics

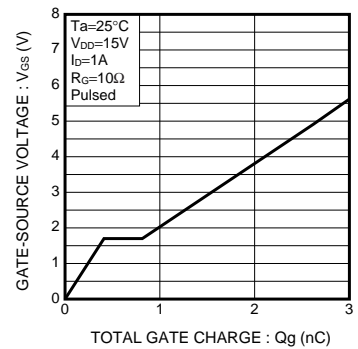


Fig.3 Dynamic Input Characteristics

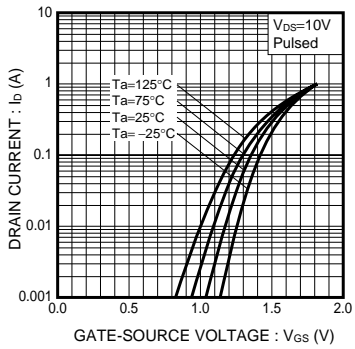


Fig.4 Typical Transfer Characteristics

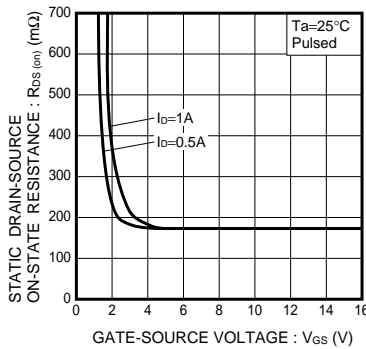


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

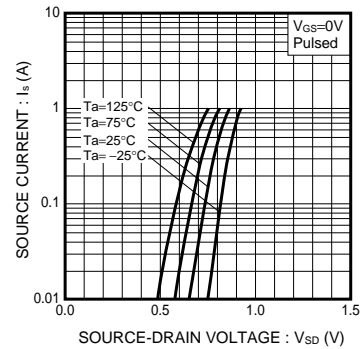


Fig.6 Source Current vs. Source-Drain Voltage

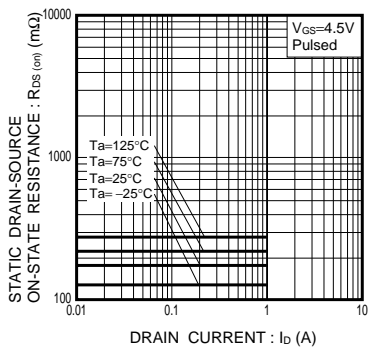


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

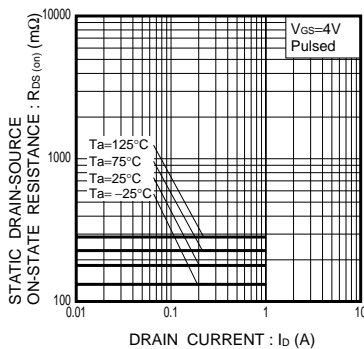


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

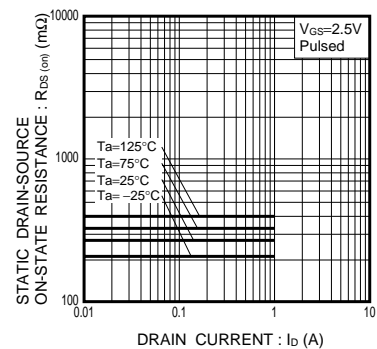


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

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